

## Power Amplifier/Antenna Switch + Low Noise Down Conversion Mixer for PHS

### Description

The CXG7003FN is a MMIC consisting of the power amplifier, diversity antenna supported switch and low noise down conversion mixer.

This IC is designed using the Sony's GaAs J-FET process featuring a single positive power supply operation.

### Features

- Operates at a single positive power supply:  $V_{DD} = 3V$
- Diversity antenna supported switch
- Small mold package: 26-pin HSOF

#### <Power amplifier/antenna switch transmitter block >

- Low current consumption:  $I_{DD} = 150mA$   
( $P_{OUT} = 20.2dBm$ ,  $f = 1.9GHz$ )
- High power gain:  $G_p = 40dB$  Typ.  
( $P_{OUT} = 20.2dBm$ ,  $f = 1.9GHz$ )

#### <Antenna switch receiver block/

#### low noise down conversion mixer>

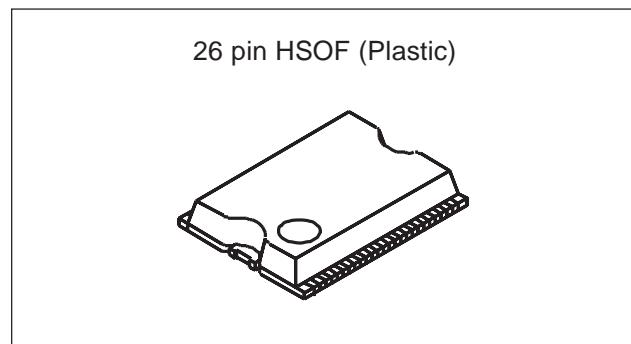
- Low current consumption:  $I_{DD} = 5.5mA$  Typ.  
(When no signal)
- High conversion gain:  $G_c = 19.5dB$  Typ. ( $f = 1.9GHz$ )
- Low distortion: Input  $IP_3 = -12dBm$  Typ. ( $f = 1.9GHz$ )
- High image suppression ratio:  $IMR = 40dBc$  Typ.  
( $f = 1.9GHz$ )
- High 1/2 IF suppression ratio:  $1/2IFR = 47dBc$  Typ.  
( $f = 1.9GHz$ )

### Applications

Digital cordless telephones (PHS)

### Structure

GaAs J-FET MMIC



### Absolute Maximum Ratings

#### <Power amplifier block>

• Supply voltage	$V_{DD}$	6	V
• Voltage between gate and source	$V_{GSO}$	1.5	V
• Drain current	$I_{DD}$	550	mA
• Allowable power dissipation	$P_D$	3	W

#### <Switch block>

• Control voltage	$V_{CTL}$	6	V
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#### <Front-end block>

• Supply voltage	$V_{DD}$	6	V
• Input power	$P_{RF}$	10	dBm

#### <Common to each block>

• Channel temperature	$T_{ch}$	150	°C
• Operating temperature	$T_{opr}$	-35 to +85	°C
• Storage temperature	$T_{stg}$	-65 to +150	°C

### Recommended Operating Conditions

#### <Common to each block>

• Supply voltage	$V_{DD}$	2.7 to 3.3	V
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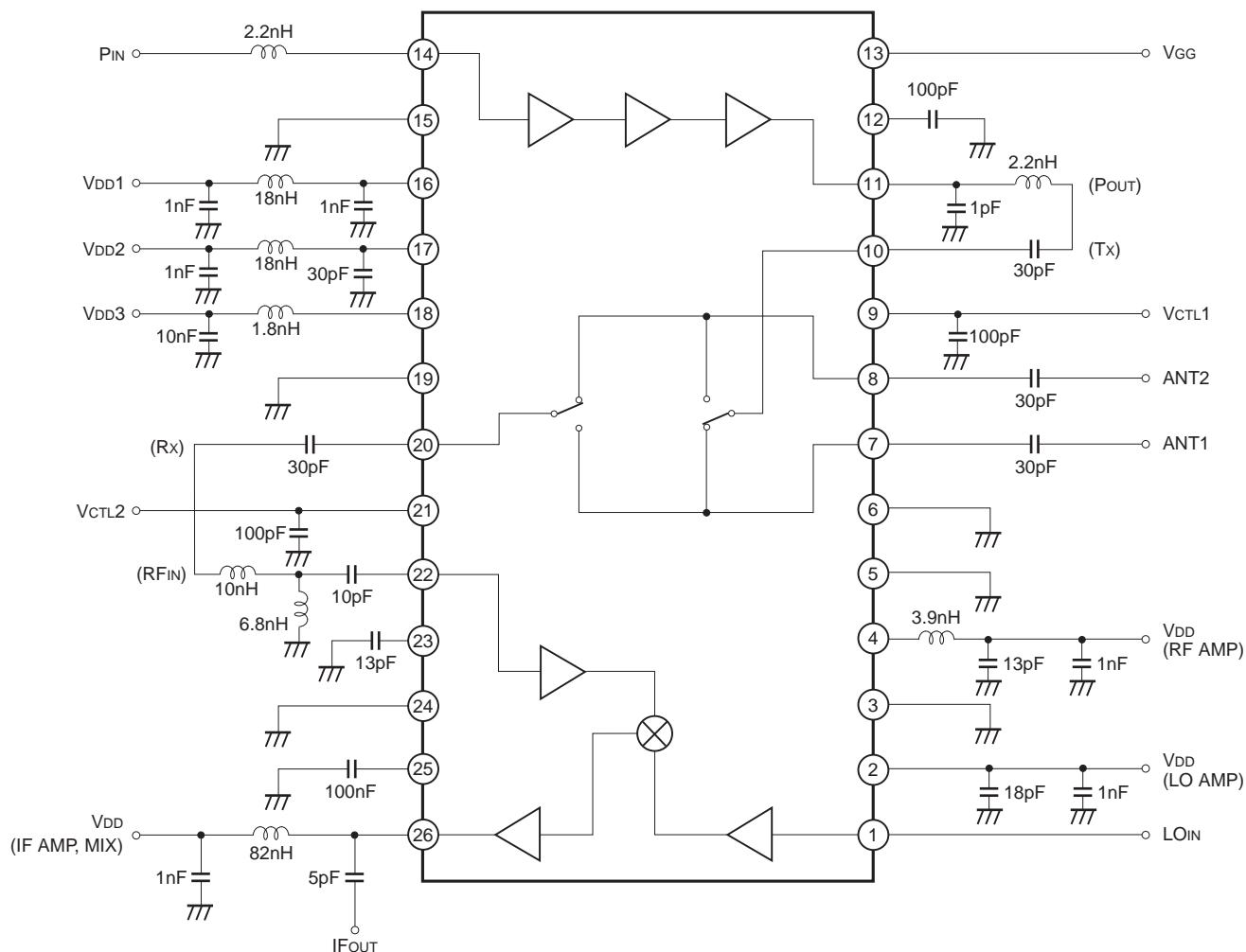
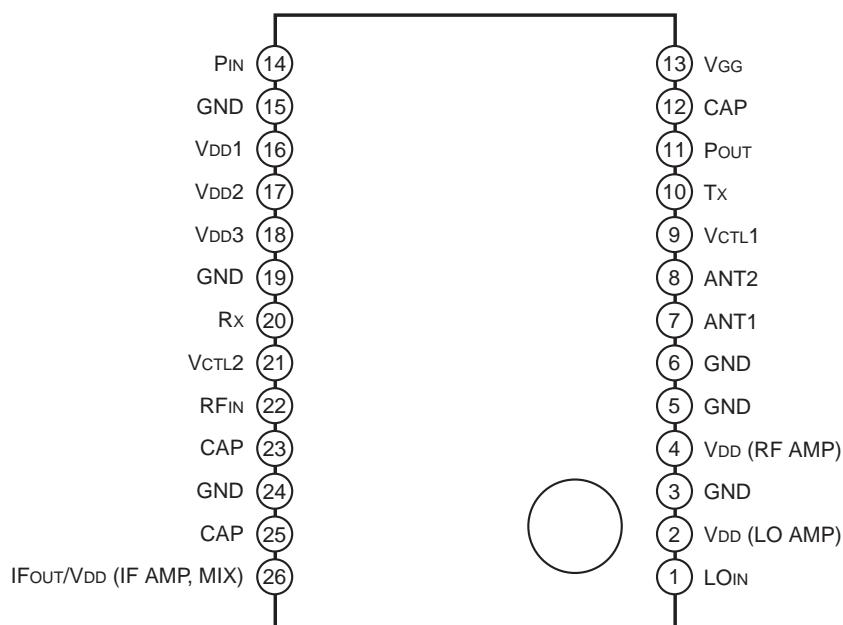
#### <Switch block>

• Control voltage (H)	$V_{CTL}(H)$	2.9 to 3.3	V
• Control voltage (L)	$V_{CTL}(L)$	0 to 0.2	V

### Notes on Handling

GaAs MMICs are ESD sensitive devices. Special handling precautions are required.

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**Block Diagram and External Circuit****Pin Configuration**

**Pin Description**

Pin No.	Symbol	Description
1	LOIN	Local signal input pin
2	V <sub>DD</sub> (LO AMP)	V <sub>DD</sub> pin of local amplifier
3	GND	GND pin
4	V <sub>DD</sub> (RF AMP)	V <sub>DD</sub> pin of RF amplifier
5	GND	GND pin
6	GND	GND pin
7	ANT1	Antenna switch pin. This pin is ANT1-Tx or ANT1-Rx by setting of V <sub>CTL1</sub> and V <sub>CTL2</sub> .
8	ANT2	Antenna switch pin. This pin is ANT2-Tx or ANT2-Rx by setting of V <sub>CTL1</sub> and V <sub>CTL2</sub> .
9	V <sub>CTL1</sub>	Antenna switch control 1 pin
10	Tx	Tx pin. Signal is input to antenna switch during ANT-Tx.
11	P <sub>OUT</sub>	Power amplifier output pin
12	CAP	Connection pin of external capacitor (for noise elimination)
13	V <sub>GG</sub>	Gate voltage adjustment pin of power amplifier (first stage, middle stage, rear-end FET)
14	P <sub>IN</sub>	Signal input pin to power amplifier
15	GND	GND pin
16	V <sub>DD1</sub>	V <sub>DD1</sub> pin of power amplifier (first stage FET)
17	V <sub>DD2</sub>	V <sub>DD2</sub> pin of power amplifier (middle stage FET)
18	V <sub>DD3</sub>	V <sub>DD3</sub> pin of power amplifier (rear-end FET)
19	GND	GND pin
20	Rx	Rx pin. ANT input signal is output to this pin during ANT1-Rx or ANT2-Rx.
21	V <sub>CTL2</sub>	Antenna switch control 2 pin
22	R <sub>F</sub> <sub>IN</sub>	RF signal input pin
23	CAP	External capacitor connection pin. This pin is connected to LNA FET source. RF amplifier characteristic is optimized during 1.9GHz by the capacitor of 13pF (Typ.).
24	GND	GND pin
25	CAP	External capacitor connection pin. IF amplifier distortion is improved by this capacitor.
26	I <sub>F</sub> <sub>OUT</sub> /V <sub>DD</sub> (IF AMP, MIX)	IF output and IF AMP, MIX V <sub>DD</sub>

## Electrical Characteristics

These specifications are when the Sony's recommended evaluation board shown on page 8 is used.

### 1. Control Pin Logic for Antenna Switch

Conditions of control pins	ANT1 – Tx ANT2 – Rx	ANT2 – Tx ANT1 – Rx
VCTL1 = 3V, VCTL2 = 0V	ON	OFF
VCTL1 = 0V, VCTL2 = 3V	OFF	ON

### 2. Power Amplifier Block + Antenna Switch Transmitter Block

These specifications are common to the ANT1 transmission and ANT2 transmission.

Unless otherwise specified:  $V_{DD} = 3V$ ,  $I_{DD} = 150mA$ ,  $P_{OUT} = 20.2dBm$ ,  $f = 1.9GHz$

When ANT1 transmission:  $V_{CTL1} = 3V$ ,  $V_{CTL2} = 0V$

When ANT2 transmission:  $V_{CTL1} = 0V$ ,  $V_{CTL2} = 3V$

( $T_a = 25^\circ C$ )

Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Current consumption	$I_{DD}$			150		mA
Gate voltage adjustment value	$V_{GG}$		0.04		0.6	V
Output power	$P_{OUT}$	Measured with the ANT pin	20.2			dBm
Power gain	$G_P$		36	40		dB
Adjacent channel leak power ratio ( $600 \pm 100kHz$ )	ACPR600kHz	Measured with the ANT pin		-63	-55	dBc
Adjacent channel leak power ratio ( $900 \pm 100kHz$ )	ACPR900kHz	Measured with the ANT pin		-70	-60	dBc
Occupied bandwidth	OBW	Measured with the ANT pin	250	275		kHz
2nd-order harmonic level	—	Measured with the ANT pin			-25	dBc
3rd-order harmonic level	—	Measured with the ANT pin			-25	dBc

### 3. Antenna Switch Receiver Block + Low Noise Down Conversion Mixer Block

These specifications are common to the ANT1 reception and ANT2 reception.

Unless otherwise specified: V<sub>DD</sub> = 3V, RF1 = 1.90GHz/-35dBm, LO = 1.66GHz/-15dBm

When ANT1 reception: V<sub>CTL1</sub> = 0V, V<sub>CTL2</sub> = 3V

When ANT2 reception: V<sub>CTL1</sub> = 3V, V<sub>CTL2</sub> = 0V

(Ta = 25°C)

Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
Current consumption	I <sub>DD</sub>	When no signal		5.5	7.5	mA
Conversion gain	G <sub>c</sub>	When a small signal	17	19.5		dB
Noise figure	NF	When a small signal		4.4	5.5	dB
Input IP3	IIP3	*1	-17	-12		dBm
Image suppression ratio	IMR	RF2 = 1.42GHz/-35dBm	25	40		dBc
1/2 IF suppression ratio	1/2IFR	RF2 = 1.78GHz/-35dBm	41	47		dBc
2 × LO-IF suppression ratio	—	RF2 = 3.08GHz/-35dBm	39	45		dBc
2 × LO+IF suppression ratio	—	RF2 = 3.56GHz/-35dBm	34	65		dBc
LO to ANT leak	P <sub>LK</sub>			-50	-40	dBm

\*1 Conversion from IM3 suppression ratio during RF1 = 1.9000GHz/-35dBm and RF2 = 1.9006GHz/-35dBm input.

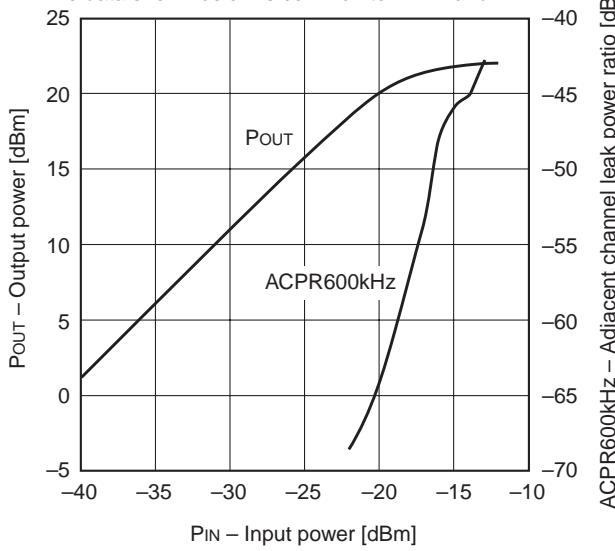
## Example of Representative Characteristics

### 1. Power Amplifier + Antenna Switch Transmitter Block ( $f = 1.9\text{GHz}$ , $T_a = 25^\circ\text{C}$ )

**P<sub>OUT</sub>, ACPR600kHz vs. P<sub>IN</sub>**

$V_{DD} = 3\text{V}$ ,  $V_{GG} = \text{const.}$ ,  
 $I_{DD} = 150\text{mA}$  (@ $P_{OUT} = 20.2\text{dBm}$ ),  
 $P_{IN} = \text{var.}$   
When ANT1 transmission:  $V_{CTL1} = 3\text{V}$ ,  $V_{CTL2} = 0\text{V}$   
When ANT2 transmission:  $V_{CTL1} = 0\text{V}$ ,  $V_{CTL2} = 3\text{V}$

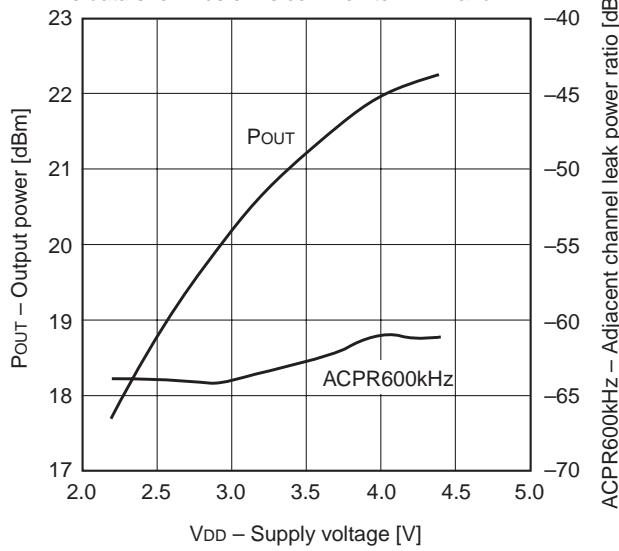
The data shown below is common to ANT1 and ANT2.



**P<sub>OUT</sub>, ACPR600kHz vs. V<sub>DD</sub>**

$V_{DD} = \text{var.}$ ,  $V_{GG} = \text{const.}$ ,  
 $I_{DD} = 150\text{mA}$  (@ $V_{DD} = 3\text{V}$ ,  $P_{OUT} = 20.2\text{dBm}$ ),  
 $P_{IN} = -19.7\text{dBm}$   
When ANT1 transmission:  $V_{CTL1} = 3\text{V}$ ,  $V_{CTL2} = 0\text{V}$   
When ANT2 transmission:  $V_{CTL1} = 0\text{V}$ ,  $V_{CTL2} = 3\text{V}$

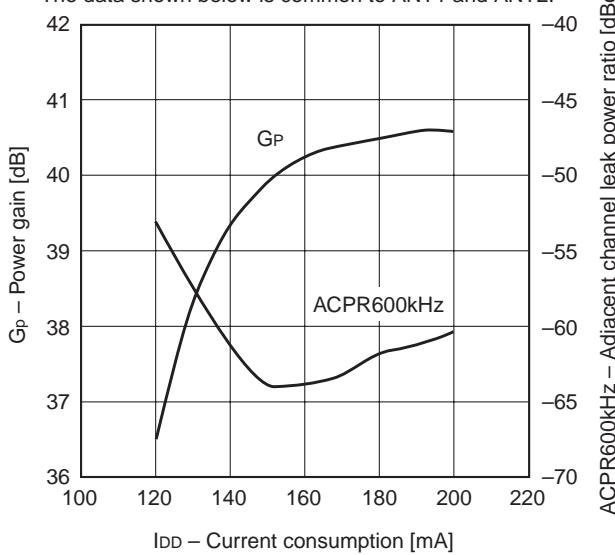
The data shown below is common to ANT1 and ANT2.



**G<sub>p</sub>, ACPR600kHz vs. I<sub>DD</sub>**

$V_{DD} = 3\text{V}$ ,  $V_{GG} = \text{var.}$ ,  $I_{DD} = \text{var.}$ ,  $P_{IN} = \text{var.}$ ,  
 $P_{OUT} = 20.2\text{dBm}$   
When ANT1 transmission:  $V_{CTL1} = 3\text{V}$ ,  $V_{CTL2} = 0\text{V}$   
When ANT2 transmission:  $V_{CTL1} = 0\text{V}$ ,  $V_{CTL2} = 3\text{V}$

The data shown below is common to ANT1 and ANT2.

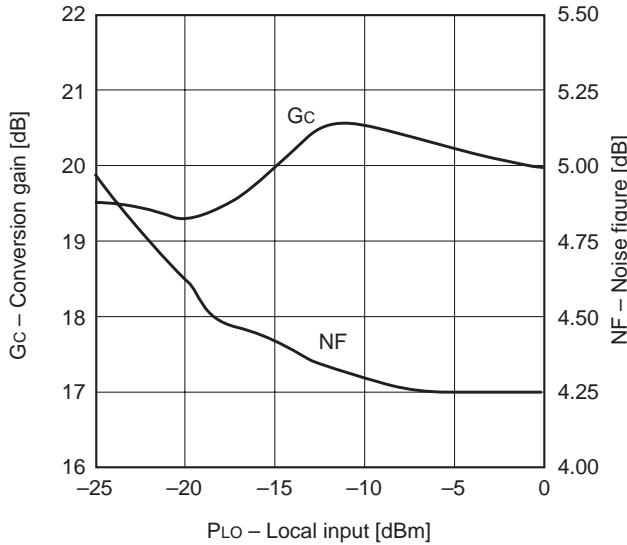


## 2. Antenna Switch Receiver Block + Low Noise Down Conversion Mixer ( $T_a = 25^\circ\text{C}$ )

### Gc, NF vs. PLo

$V_{DD} = 3V$ , RF1 = 1.90GHz/small signal,  
 $\text{LO} = 1.66\text{GHz}$   
When ANT1 reception:  $V_{CTL1} = 0V$ ,  $V_{CTL2} = 3V$   
When ANT2 reception:  $V_{CTL1} = 3V$ ,  $V_{CTL2} = 0V$

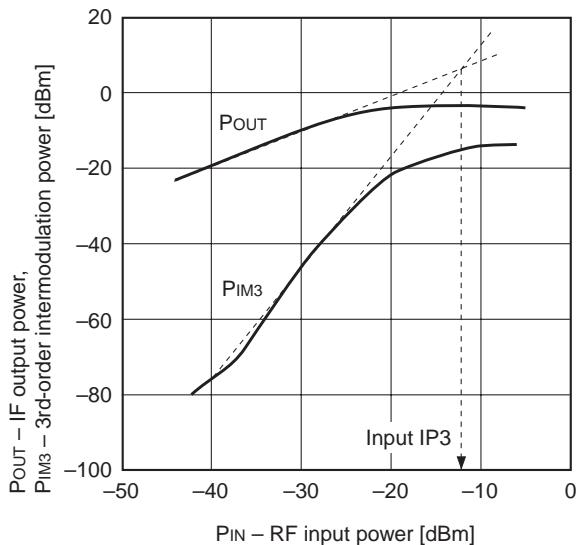
The data shown below is common to ANT1 and ANT2.



### POUT, PIM3 vs. PIN

$V_{DD} = 3V$ , RF1 = 1.9000GHz, RF2 = 1.9006GHz,  
 $\text{LO} = 1.66\text{GHz}/-15\text{dBm}$   
When ANT1 reception:  $V_{CTL1} = 0V$ ,  $V_{CTL2} = 3V$   
When ANT2 reception:  $V_{CTL1} = 3V$ ,  $V_{CTL2} = 0V$

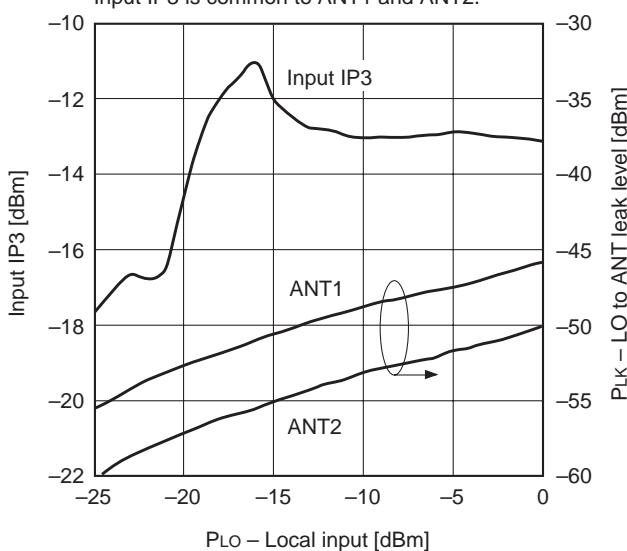
The data shown below is common to ANT1 and ANT2.



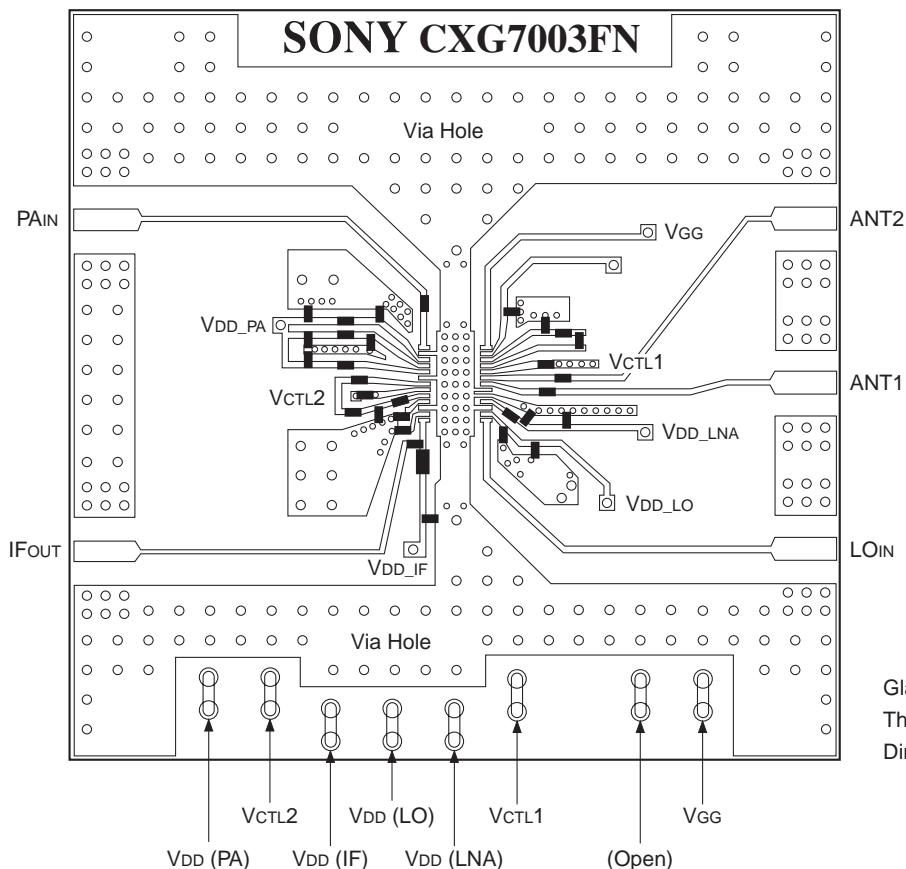
### Input IP3, PLK vs. PLo

$V_{DD} = 3V$ , RF = 1.90GHz/-35dBm,  
 $\text{LO} = 1.66\text{GHz}$   
When ANT1 reception:  $V_{CTL1} = 0V$ ,  $V_{CTL2} = 3V$   
When ANT2 reception:  $V_{CTL1} = 3V$ ,  $V_{CTL2} = 0V$

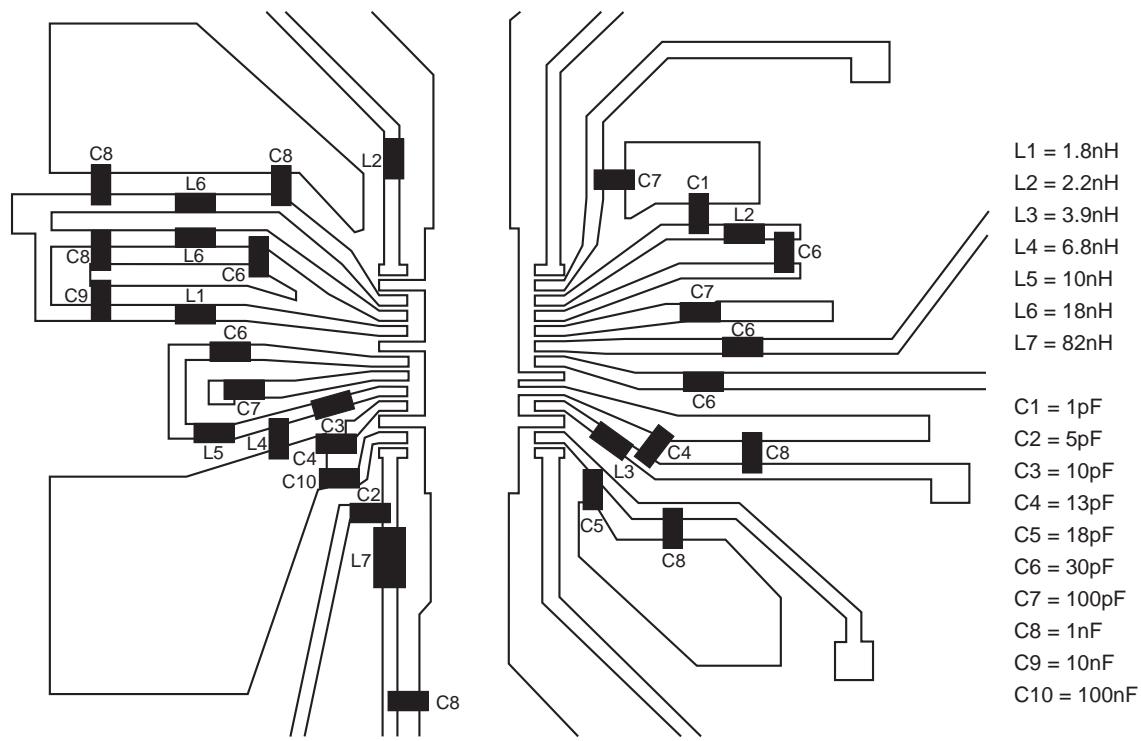
Input IP3 is common to ANT1 and ANT2.



## Recommended Evaluation Board



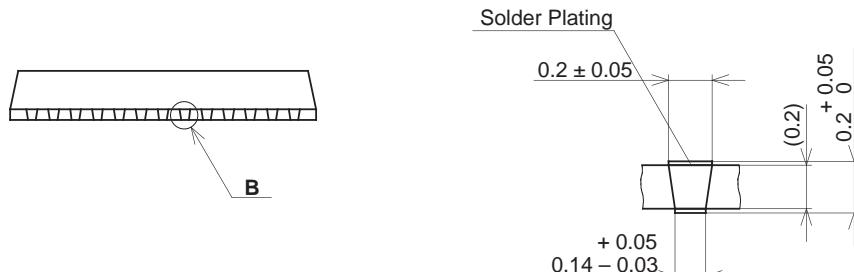
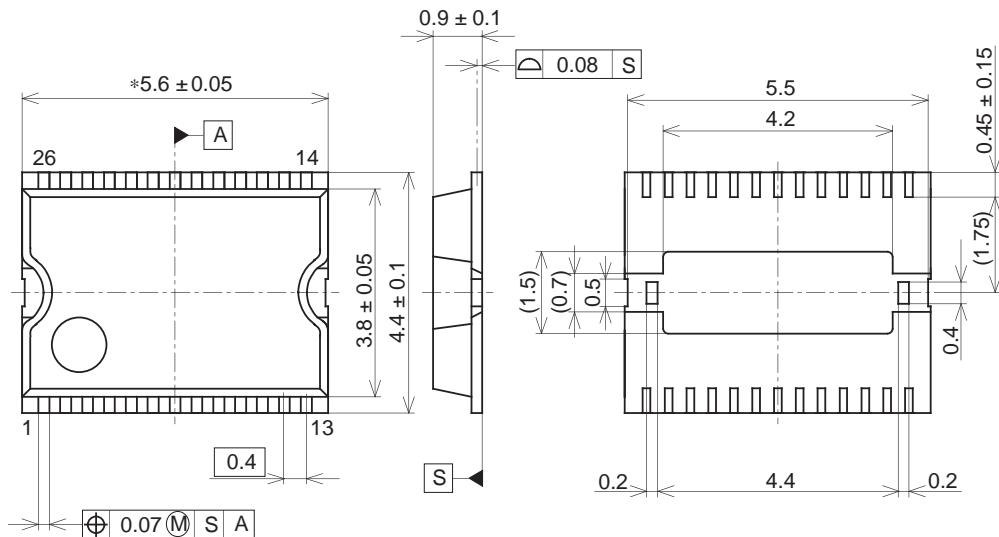
## Enlarged Diagram of External Circuit Block



## Package Outline

Unit: mm

## HSOF 26PIN (PLASTIC)



NOTE: Dimension "\*" does not include mold protrusion

## PACKAGE STRUCTURE

SONY CODE	HSOF-26P-01
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.06g

## **LEAD PLATING SPECIFICATIONS**

ITEM	SPEC.
LEAD MATERIAL	COPPER ALLOY
SOLDER COMPOSITION	Sn-Bi Bi:1-4wt%
PLATING THICKNESS	5-18μm